

Silicon PNP Power Transistor

2SA1185

DESCRIPTION

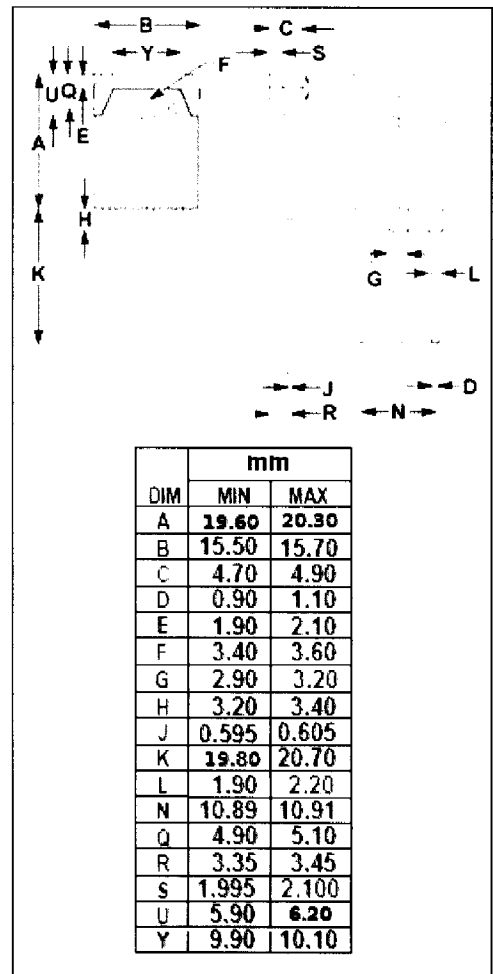
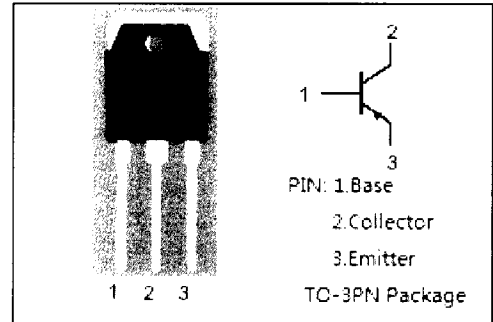
- Collector-Emitter Breakdown Voltage-
 : $V_{(BR)CEO} = -50V(\text{Min.})$
- Low Collector-Emitter Saturation Voltage-
 : $V_{CE(sat)} = -0.8V(\text{Max.}) @ I_C = -7A$
- Good Linearity of h_{FE}
- Large Collector Current

APPLICATIONS

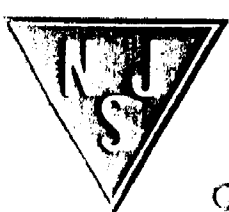
- Designed for high power audio frequency amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-7	A
I_{CM}	Collector Current-Peak	-15	A
I_{BM}	Base Current-Peak	-5	A
P_C	Collector Power Dissipation @ $T_C=25^\circ C$	60	W
	Collector Power Dissipation @ $T_a=25^\circ C$	2.5	
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}; I_B = 0$	-50			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -7\text{A}; I_B = -0.7\text{A}$			-0.8	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -7\text{A}; V_{CE} = -5\text{V}$			-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -50\text{V}; I_E = 0$			-1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-2	mA
h_{FE-1}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -5\text{V}$	60		320	
h_{FE-2}	DC Current Gain	$I_C = -7\text{A}; V_{CE} = -5\text{V}$	20			
C_{OB}	Collector Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f = 1\text{MHz}$		250		pF
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -5\text{V}$		100		MHz

◆ h_{FE-1} Classifications

Q	P	O
60-120	100-200	160-320